SPECIFICATION AMENDMENTS

Replace the paragraph beginning at page 1, line 10 with:

~~In a waveguide layer of an~~ An end face ~~portion~~, including a waveguide layer, of a semiconductor laser device or a semiconductor optical device, such as an optical modulator, is generally coated with a reflecting film ~~is generally coated~~. When ~~a film thickness d of~~ a reflecting film ~~(coating film:~~ having a refractive index n_1~~) formed~~ on the end face portion of the semiconductor element ~~is made odd number times~~ has a thickness d equal to an odd integer multiple of $\lambda/(4n_1)$, the reflectance of the reflecting film becomes ~~the~~ a minimum value. In addition, when a coating ~~film~~ having a refractive index which is a square root of a refractive index n_c of a laminated element ~~including~~ is on a waveguide layer at the end face portion is ~~formed~~, an antireflecting film ~~can be~~ is obtained. For example, the reference of I. Ladany, et al., "Scandium oxide antireflection coatings for superluminescent LEDs", Appl. Opt. Vol. 25, No. 4, pp. 472-473, (1986), describes a semiconductor laser ~~in which a reflecting~~ with an antireflection film on the end face ~~is antireflected~~.

Replace the paragraph beginning at page 1, line 22 with:

Wavelength dependence of ~~a~~ reflectance of a ~~single layer~~ reflecting film (refractive index $n_1 = 1.449$) ~~formed to have~~ including films of various ~~film thickness~~ thicknesses in a laminated element (effective refractive index $n_c = 3.37$), including a waveguide layer of an end face portion of a semiconductor optical device, will be considered. In this case, the reflectance is set to be the minimum value at a setting wavelength $\lambda = 980$ nm. When the reflectance is the minimum value, the ~~film~~ thickness is ~~odd number times~~ an odd interger multiple of $\lambda/(4n_1)$. ~~When the case in which~~ If the single-layer reflecting film has a ~~film~~ thickness of $\lambda/(4n_i)$ and ~~the case in which~~ if the single-layer reflecting film has a ~~film~~ thickness of $5\lambda/(4n_1)$ ~~are considered~~, it is understood that a flat portion near a minimal value of the reflectance in the single-layer reflecting film having the ~~film~~ thickness of $\lambda/(4n_1)$ is larger than that in the single-layer reflecting film having the ~~film~~ thickness of $5\lambda/(4n_1)$.

Replace the paragraph beginning at page 2, line 9 with:

When a ~~film~~ thickness d of the reflecting film on the end face portion of the semiconductor optical device is increased an odd-number of times $\lambda/(4n_1)$, a wavelength band of a low-reflectance area near the minimal value of the reflectance becomes narrow, and a

semiconductor laser characteristic disadvantageously ~~largely~~ varies ~~under the influence of~~ significantly due to the wavelength dependence of the reflectance of the reflecting film.